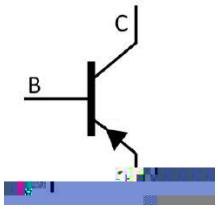
WR0<50P ΜΜÞ SQS ÆṀч s ll ㄱ Silicon PNP transistor in a TO-92LM Plastic Package.

ت ᄐ я ∪ Ӈ/Ã ћ`Н ђ˜ /љ NWF653< Й ´
Low collector saturation, high speed switching time, complementary to KTC3209.

ᵮ ı ' ѽ ᵌ/ↄ ◊ Ã ћ
Power amplifier and switching applications.



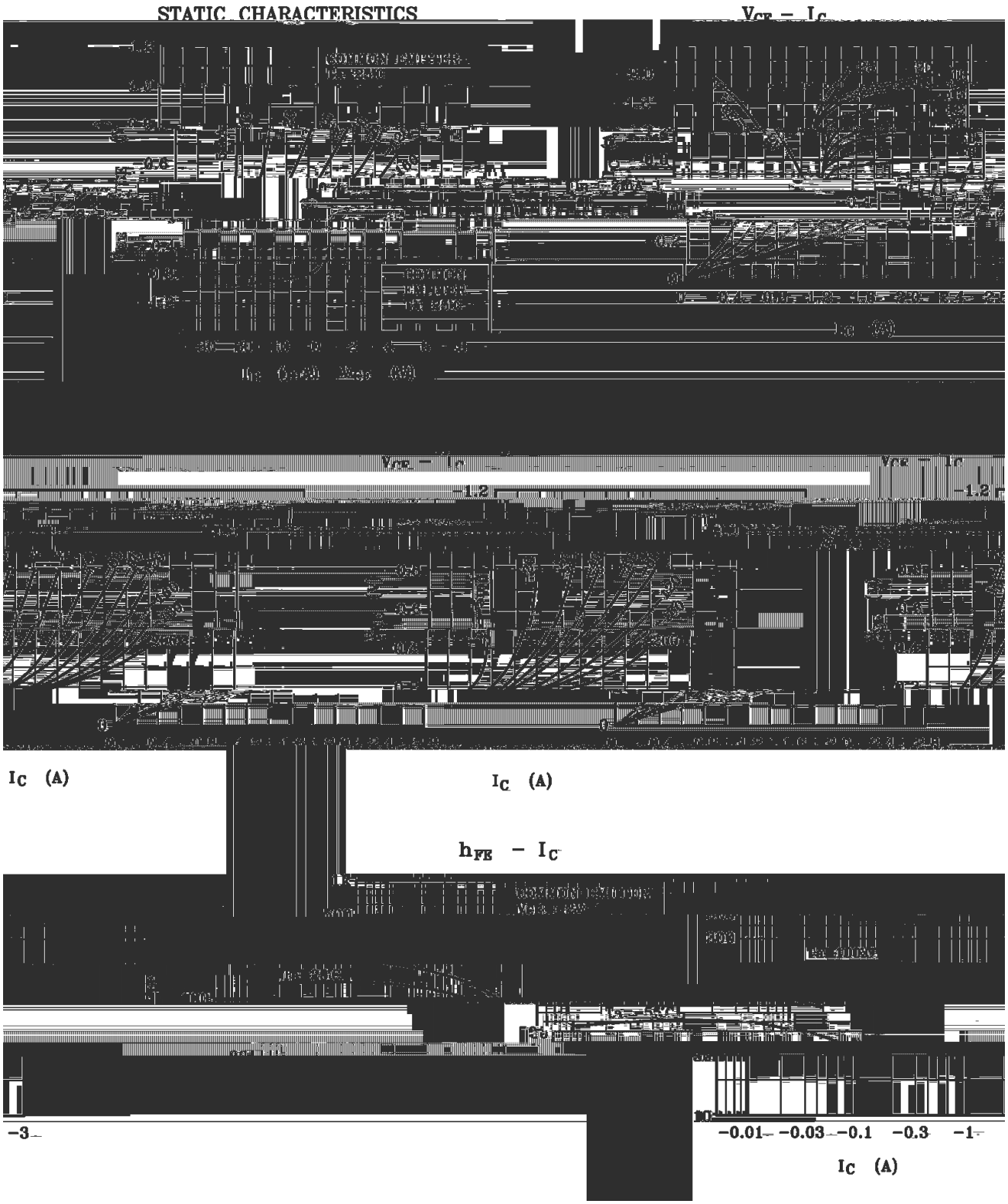


PIN1 χ Base PIN 2 χ Collector -1382alec4lec040607e71 Tf2.2229 0 TD0 Tf1 Tf2.2229 0 T4MarE73

v ̈Ω Parameter	↰ N Symbol	̈Ω Ö Rating	D Ђ Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

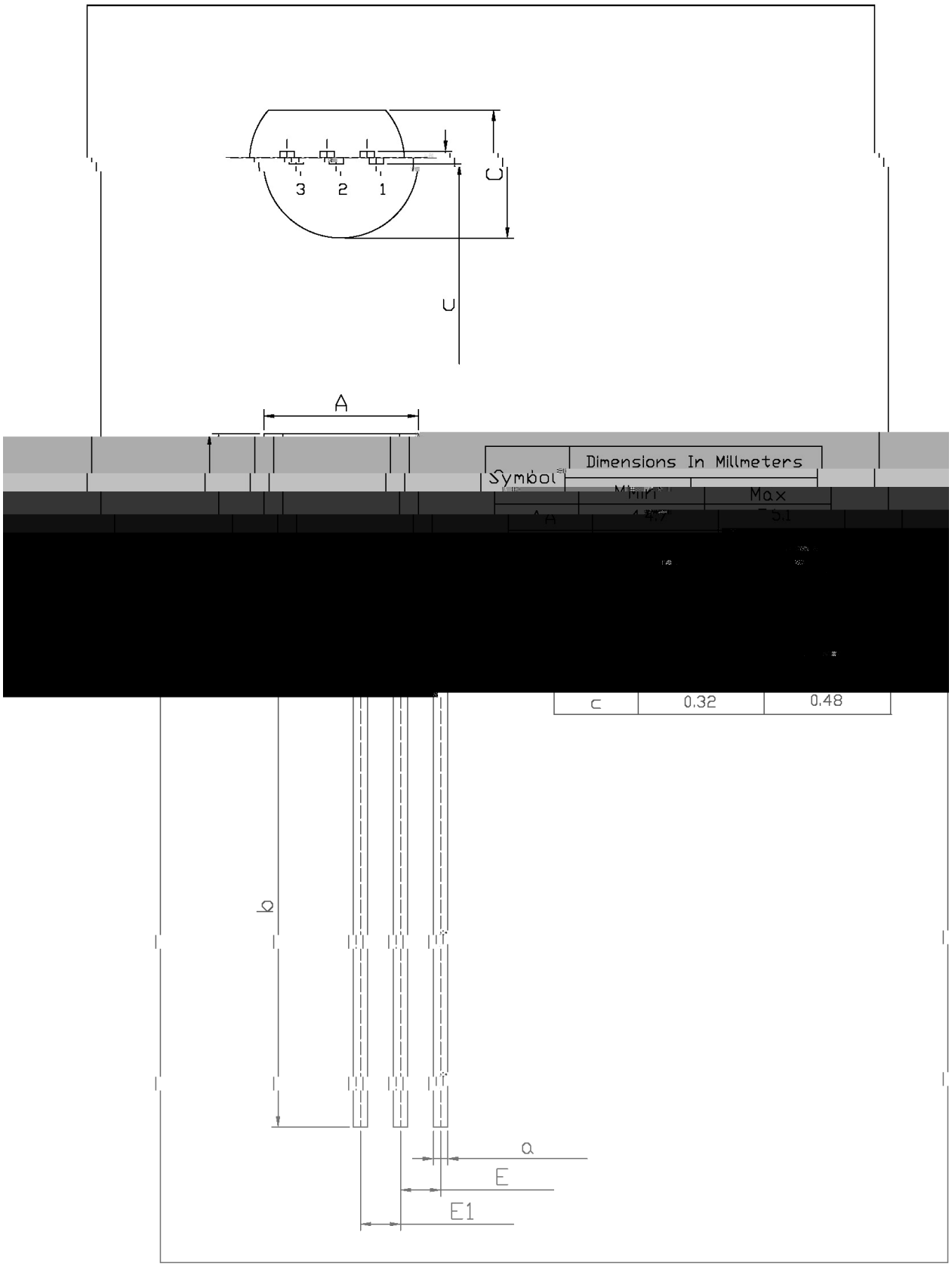
v ̈Ω Parameter	↰ N Symbol	╨ ⁝ ̊ ţ Test Conditions	ϣ ṇ Ö ε ʒ Ö Min

/ Electrical Characteristic Curve

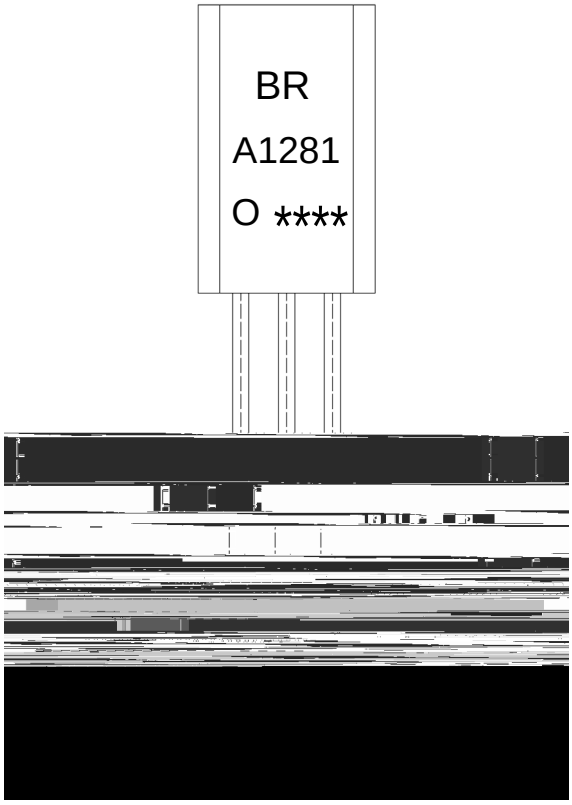


/ Package Dimensions

TO-92LM Unit: mm

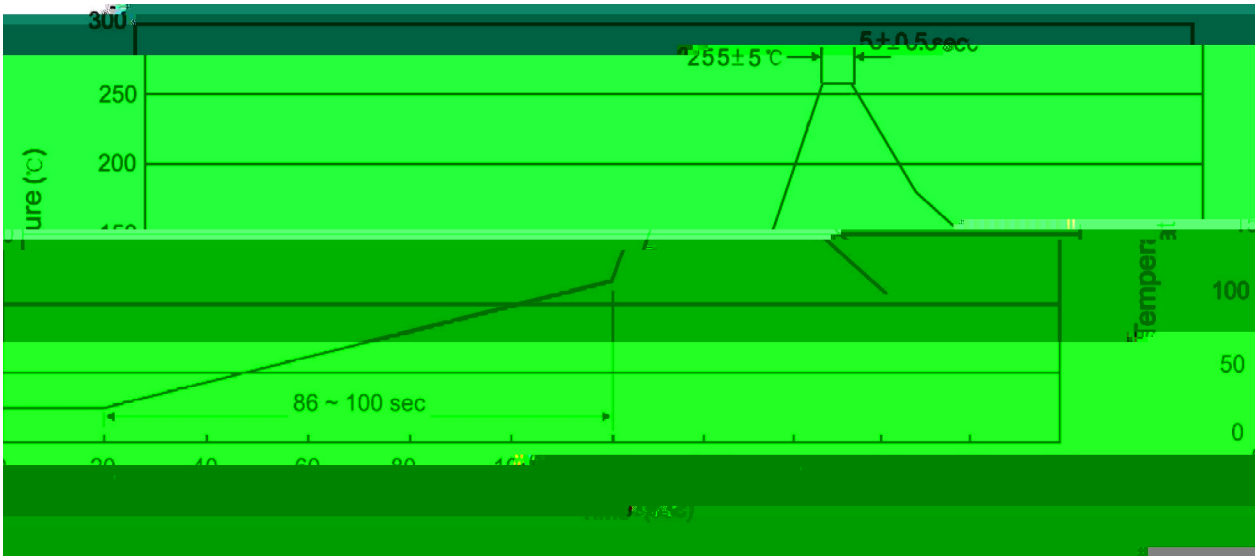


/ Marking Instructions



ب ″ χ	
EU=	ﻫ ﺯ ﻧ ﮦ
D45 ; 4 χ	ﻫ ﺯ ﻦ ﮦ
R=	ﻫ k ﺎ ﻫ ' ⁶ ﮦ
---- χ	ﻫ ﺍ ﻓ ﻩ ﻦ ﮦ ﺍ ﻫ ﺍ ﻓ ﻩ ﻦ ﻳ ﻕ
Note:	
BR:	Company Code.
A1281:	Product Type.
O:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı `H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ł ı `H ڑ `Y ﾊ ㎛ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ɔ ﻉ ỷ ㎛ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ł `H ڑ χ 10 ° 1 sec. Temp.:270 ° 5 ł Time:10 ° 1 sec

/ Packaging SPEC.

ˈQ ţ ﾘ Ł / BULK

Package Type	Units					Dimension		(unit mm3)
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92LM	1,000	8	8,000	5	40,000	135×190	237×172×102	560×245×195

ﾊ Ⅴ ﾘ Ł / AMMO

Package Type	Units					Dimension	(unit mm3)
	Units/tape /	Tape/Inner Box /	Rows/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Inner Box	Outer Box
TO-92LM	2,500	1	100	10	25,000	328×230×42	480×346×235 547×407×268

/ Notices